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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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10/648,183

08/25/2003

Byung-Seop Hong

51876P352

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07/26/2005

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EXAMINER

DANG, TRUNG Q

ART UNIT

PAPER NUMBER

2823

DATE MAILED: 07/26/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

## Office Action Summary

Application No.

10/648,183

Applicant(s)

HONG ET AL.

Examiner

Trung Dang

Art Unit

2823

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

### Status

- 1) ☒ Responsive to communication(s) filed on 20 June 2005.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

### Disposition of Claims

- 4) ☒ Claim(s) 1-23 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1,2,8,14 and 15 is/are rejected.
- 7) ☒ Claim(s) 3-7,9-13,16-23 is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

### Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
  - ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.

### Attachment(s)

- |                                                                                                                        |                                                                                         |
|------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892)                                                       | 4) <input type="checkbox"/> Interview Summary (PTO-413)<br>Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)                                   | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)             |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)<br>Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____                                                |

**DETAILED ACTION**

***Claim Rejections - 35 USC § 103***

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1, 2 and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lee (US Pat. 6,599,821) in view of Wu (US Patent 6,455,383) and Eichman et al. (US Pat. 5,308,655), all of record.

Lee teaches a method for fabricating a semiconductor device comprising the steps of:

forming a stack layer of a gate layer (201), a poly-silicon layer (202), a tungsten layer (203), and a hard mask (204) sequentially deposited on a semiconductor substrate (200);

carrying out a selective oxidation process adopting a rapid thermal process (RTP), wherein the poly-silicon layer (202) of the stack is only oxidized;

and forming a gate sealing insulation layer (208) on the heat treated stack layer.

See Fig. 2D and related text for the materials of layers 202 and 203. See col. 4, lines 13-14 for the selective oxidation process adopting a RTP. See col. 4, lines 21-25 for the selective oxidation process the annealing step (corresponds to the claimed heat

treatment process) are performed simultaneously. Note that, since the selective oxidation process of claim 1 and the selective oxidation process of the prior art are both performed by carrying a RTP, a stress caused by the RTP would inherently occur, absent evident to the contrary. Furthermore, since the selective oxidizing process and the annealing process of the reference are simultaneously performed, the stress exerted during the selective oxidizing process would inherently released by the annealing process, absent evidence to the contrary.

Lee differs from the claim in not disclosing that insulating sidewall spacer 208 is of a nitride layer.

Wu teaches that gate sidewall spacers of silicon nitride are formed by LPCVD (col. 10, lines 3-4).

It would have been obvious to one of ordinary skill in the art to form the insulating sidewall spacer 208 in Lee by depositing a LPCVD silicon nitride layer as suggested by Wu because such LPCVD process to form nitride sidewall spacers is known in the art, and the application of a known process to made the same would have been within the level of one skilled in the art.

The combination of Lee and Wu including an annealing step (corresponds to the claimed heat treatment process) and a nitride spacer deposition step by LPCVD (corresponds to the claimed forming a gate sealing nitride layer) is now differs from the claim in not disclosing a) the annealing step and the nitride deposition step are carried out by using LPCVD furnace under an in-situ method (claim 2), and b) the annealing

step and the nitride deposition step are carried out in two different LPCVD furnaces under an ex-situ method (claim 8).

Eichman et al. teach a process in which a deposition step of a nitride layer and an annealing step can be carried out under an in-situ method (col. 2, line 63) or, alternatively, the deposition step and the annealing step can be carried out in two different LPCVD furnaces under an ex-situ method (col. 3, lines 46-49).

It would have been obvious to one of ordinary skill in the art to modify the teaching of the combination by carrying out the annealing step and the deposition step of the LPCVD nitride spacer 208 (resulted in the combined process of Lee and Wu) under an in-situ method or an ex-situ method because it is known that in situ processing is desirable for minimizing exposure of the wafer to particulates and oxygen outside the process chamber environment, and the ex-situ method is taught to produce the same result as in the in-situ method provided that the environment outside process chambers is controlled in a non-contaminated condition. Note that the process of the combination results in an annealing step being performed in a LPCVD furnace as recited in claim 1 because the annealing step and the step for depositing the LPCVD nitride spacer 208 are performed in-situ or ex-situ as mentioned above.

3. Claims 14 and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wu (US Pat. 6,455,383) in view of Eichman et al. (US. Pat. 5,308,655), all of record.

Wu teaches a method for fabricating a semiconductor device comprising the steps of:

forming a stack layer of a gate oxide layer (301a), a poly-silicon layer (302a), a tungsten layer (306a), and a hard mask (307a) sequentially deposited on a semiconductor substrate (300);

selectively oxidizing only the poly-silicon layer (302a) of the stack layer;

depositing a gate sealing nitride layer (312a) by **LPCVD** on the selectively oxidized stack layer;

and performing a rapid thermal annealing (RTA).

See Fig. 4D(a) and related text for the materials of layers 301a, 302a, 306a, and 307a. See col. 9, lines 27-29 for the claimed step of selectively oxidizing only the poly-silicon layer (302a) of the stack layer to form oxide layer 309a in Fig. 4E(a). See paragraph bridging column 9 and column 10 for the claimed steps of depositing a gate sealing nitride layer (312a) of Fig. 4F(a) by **LPCVD** on the selectively oxidized stack layer and heat treating the stack layer. Note that, the rapid thermal annealing (**RTA**) (corresponds to the claimed limitation "heat treatment") to redistribute implanted doping impurities also known in the art as for activating source/drain regions (col. 10, lines 1-2) would inherently release stress exerted during the selective oxidizing and gate sealing nitride layer depositing, absent evidence to the contrary. Furthermore, step d3) and step e) of claim 14 do not necessarily mean two distinct steps, hence the **RTA** process of the reference reads on both step d3 and e.

Wu differs from the claim in not disclosing that the deposition of gate sealing nitride layer and the **RTA** are carried out in the identical furnace or in two different LPCVD furnaces under an ex-situ method as claimed in claim 15.

Eichman et al. teach a process in which a deposition step of a nitride layer and an annealing step following the deposition step can be carried out under an in-situ method (col. 2, line 63) or, alternatively, the deposition step and the annealing step can be carried out in two different LPCVD furnaces under an ex-situ method (col. 3, lines 46-49).

It would have been obvious to one of ordinary skill in the art to modify Wu's teaching by carry out the LPCVD of gate sealing nitride layer 312a and the **RTA** step under an in-situ method (i.e., identical furnace) or an ex-situ method (i.e., two different LPCVD furnaces) as suggested by Eichman because it is known that in situ processing is desirable for minimizing exposure of the wafer to particulates and oxygen outside the process chamber environment, and the ex-situ method is taught to produce the same result as in the in-situ method provided that the environment outside process chambers is controlled in a non-contaminated condition. Note that the combined process results in the **RTA** step of Wu that is readable on both step d3 and step e) being performed in an LPCVD furnace as recited in claim 14.

***Allowable Subject Matter***

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4. Claims 3-7, 9-13 and 16-23 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

5. The following is a statement of reasons for the indication of allowable subject matter:

Claim 3 and its dependent claims are allowable over prior art of record because prior art fails to teach or suggest, either singly or in combination, the claimed limitations regarding increasing LPCVD furnace temperature from room temperature to a target temperature and keeps the target temperature in a vacuum ambient in the heat treating step and then decreasing the LPCVD furnace temperature from the target temperature for the heat treating to a target temperature for depositing the gate sealing nitride layer in the step of depositing the gate sealing nitride layer.

Claim 9 and its dependent claims are allowable because prior art of record fails to teach or suggest the claimed limitations regarding the heat treating is performed by increasing a temperature of a first LPCVD furnace from room temperature to a target temperature and keeping the target temperature in a vacuum ambient and then unloading the substrate after decreasing the temperature of the first LPCVD furnace to room temperature, and depositing the gate sealing nitride layer after moving the unloaded substrate in the first LPCVD furnace to a second LPCVD furnace.



Claim 16 and its dependent claims are allowable because prior art of record fails to teach or suggest the claimed limitations regarding depositing the gate sealing nitride layer in a first LPCVD furnace and heat treating the substrate in a second LPCVD furnace by increasing a temperature of the second LPCVD furnace from room temperature to a target temperature and keeping the target temperature in a vacuum or inert gas ambient and then unloading the substrate after decreasing the temperature of the second LPCVD furnace to room temperature.

Claim 17 and its dependent claims are allowable because prior art of record fails to teach or suggest the claimed limitations regarding depositing the gate sealing nitride layer in the LPCVD furnace then heat treating the substrate in an annealing furnace by increasing a temperature of the annealing furnace from room temperature to a target temperature and keeping the target temperature in a vacuum or inert gas ambient and unloading the substrate after decreasing the temperature of the annealing furnace.

### ***Response to Arguments***

6. Applicant's arguments with respect to claims 1, 2, 8, 14 and 15 have been considered but are moot in view of the new ground(s) of rejection.
7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Trung Dang whose telephone number is 571-272-1857. The examiner can normally be reached on Mon-Friday 9:30am-6:00pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



Trung Dang  
Primary Examiner  
Art Unit 2823

07/25/05